

SAMYANG ELECTRONICS

(SINGLE CHIP)

MBR1620 --- MBR16200

SCHOTTKY BARRIER RECTIFIER

FEATURES

- \bigotimes Metal-semiconductor junction with guard ring
- \bigcirc Epitaxial construction
- $\bigotimes \mathsf{Low}$ forward voltage drop,low switching losses
- \bigcirc High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- \bigcirc The plastic material carries U/L $\,$ recognition 94V-0 $\,$

MECHANICAL DATA

- - MIL-STD-750,Method 2026
- ◇Polarity: As marked
- ♦ Weight: 0.08ounces, 2.24 grams
- ♦ Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

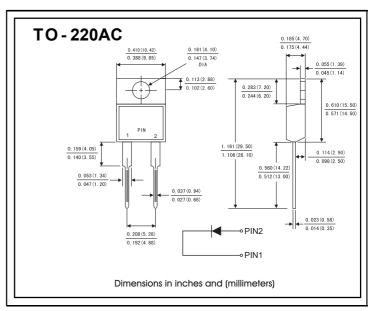
		Symbols	MBR 1620	MBR 1630	MBR 1640	MBR 1650	MBR 1660	MBR 1680	MBR 16100	MBR 16150	MBR 16200	Units
Maximum repetitive peak reverse voltage		Vrrm	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage		Vrms	14	21	28	35	42	56	70	105	140	Volts
Maximum DC blocking voltage		VDC	20	30	40	50	60	80	100	150	200	Volts
Maximum average forward rectified current See Fig. 1		I(AV)	16.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		FSM	200.0								Amps	
Maximum instantaneous forward voltage at 16.0 A		VF	0. 60			(0.75	0.85		0.90	0.95	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	°c=25°C		0.2									mA
	「 _c =125°C	R	30 50									
Typical thermal resistance (Note 2)		R_{θ} JC	3.0									° C/W
Operating junction temperature range		TJ	-65 to+150									°C
Storage temperature range		Tsig	-65 to+150									°C

NOTE: 1. Pulse test: 300us pulse width, 1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient

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RATINGS AND CHARACTERISTIC CURVES

